NEC

MOS FIELD EFFECT TRANSISTOR
μPA1910

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

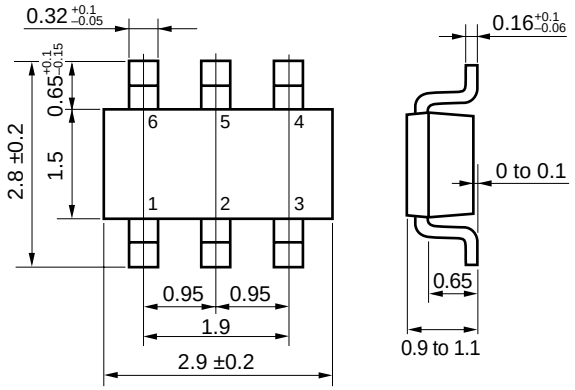
The μPA1910 is a switching device which can be driven directly by a 2.5-V power source.

The μPA1910 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- Can be driven by a 2.5-V power source
- Low on-state resistance
  $R_{DS(on)1}$ = 80 mΩ MAX. (V_{GS} = –4.5 V, I_D = –1.5 A)
  $R_{DS(on)2}$ = 90 mΩ MAX. (V_{GS} = –4.0 V, I_D = –1.5 A)
  $R_{DS(on)3}$ = 100 mΩ MAX. (V_{GS} = –3.0 V, I_D = –1.0 A)
  $R_{DS(on)4}$ = 130 mΩ MAX. (V_{GS} = –2.5 V, I_D = –1.0 A)

PACKAGE DRAWING (Unit : mm)



1, 2, 5, 6 : Drain
3 : Gate
4 : Source

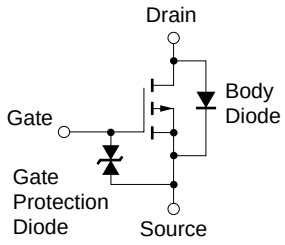
★ ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1910TE	6-pin Mini Mold (Thin Type)

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

	Drain to Source Voltage	V_{DSS}	–12	V
	Gate to Source Voltage	V_{GSS}	–10/+5	V
	Drain Current (DC)	$I_{D(DC)}$	±2.5	A
	Drain Current (pulse) Note1	$I_{D(pulse)}$	±10	A
★	Total Power Dissipation	P_{T1}	0.2	W
	Total Power Dissipation Note2	P_{T2}	2	W
	Channel Temperature	T_{ch}	150	°C
	Storage Temperature	T_{stg}	–55 to +150	°C

EQUIVALENT CIRCUIT



Marking: TB

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1 %

2. Mounted on FR-4 board, t ≤ 5 sec.

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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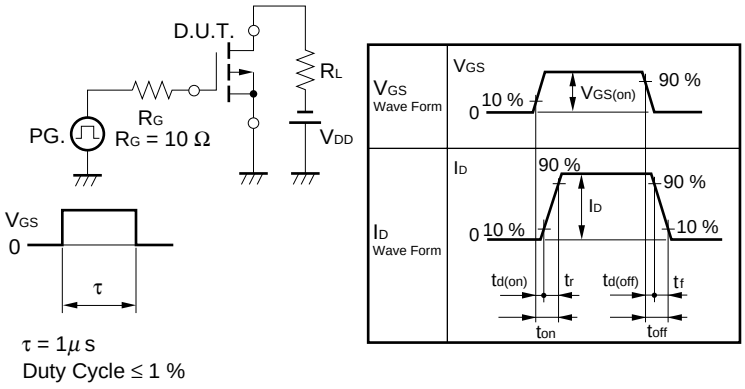
The mark ★ shows major revised points.

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

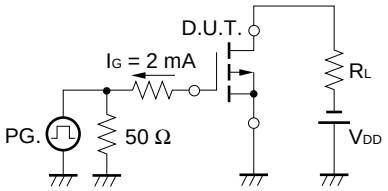
	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –12 V, V_{GS} = 0 V			–10	μA
	Gate Leakage Current	I_{GSS}	V_{GS} = ±10 V, V_{DS} = 0 V			±10	μA
	Gate to Source Cut-off Voltage	$V_{GS(off)}$	V_{DS} = –10 V, I_D = –1 mA	–0.4	–0.72	–1.5	V
	Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = –10 V, I_D = –1.5 A	1	5.1		S
	Drain to Source On-state Resistance	$R_{DS(on)1}$	V_{GS} = –4.5 V, I_D = –1.5 A		60	80	mΩ
		$R_{DS(on)2}$	V_{GS} = –4.0 V, I_D = –1.5 A		63	90	mΩ
		$R_{DS(on)3}$	V_{GS} = –3.0 V, I_D = –1.0 A		75	100	mΩ
		$R_{DS(on)4}$	V_{GS} = –2.5 V, I_D = –1.0 A		86	130	mΩ
	Input Capacitance	C_{iss}	V_{DS} = –10 V		386		pF
	Output Capacitance	C_{oss}	V_{GS} = 0 V		283		pF
	Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		154		pF
	Turn-on Delay Time	$t_{d(on)}$	V_{DD} = –10 V		131		ns
	Rise Time	t_r	I_D = –1.5 A		603		ns
	Turn-off Delay Time	$t_{d(off)}$	$V_{GS(on)}$ = –4.0 V		427		ns
	Fall Time	t_f	R_G = 10 Ω		1470		ns
	Total Gate Charge	Q_G	V_{DD} = –10 V		6.7		nC
	Gate to Source Charge	Q_{GS}	I_D = –3.0 A		1.6		nC
	Gate to Drain Charge	Q_{GD}	V_{GS} = –4.0 V		2.9		nC
	Diode Forward Voltage	$V_{F(S-D)}$	I_F = 2.5 A, V_{GS} = 0 V		0.74		V
★	Reverse Recovery Time	t_{rr}	I_F = 2.5 A, V_{GS} = 0 V		30.0		ns
★	Reverse Recovery Charge	Q_{rr}	di/dt = 10 A/μs		2.2		nC

★ **TEST CIRCUIT 1 SWITCHING TIME**



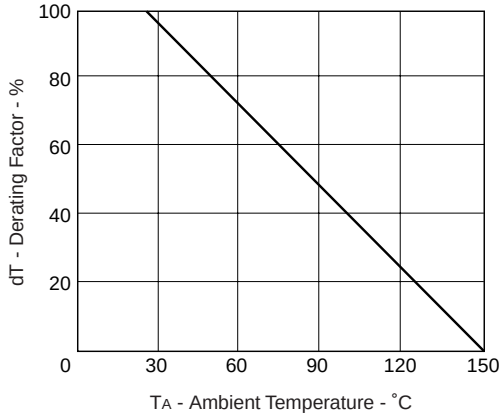
τ = 1μs
Duty Cycle ≤ 1 %

★ **TEST CIRCUIT 2 GATE CHARGE**

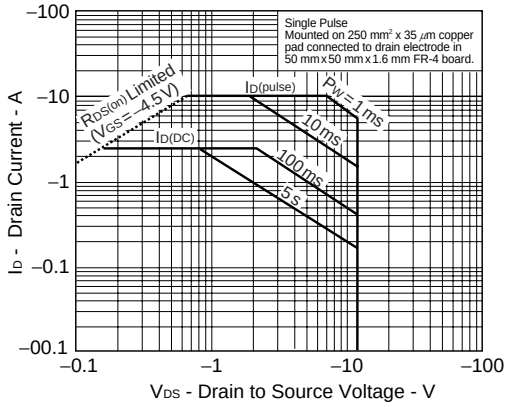


★ TYPICAL CHARCTERISTICS (T_A = 25 °C)

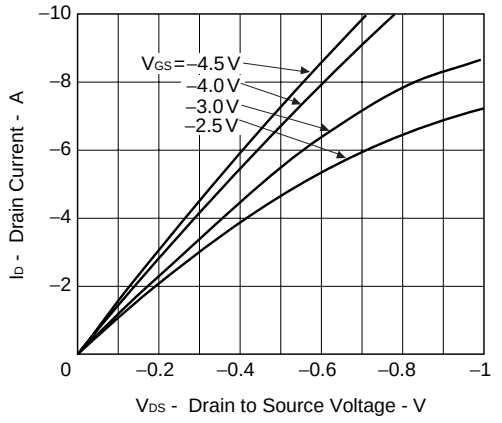
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



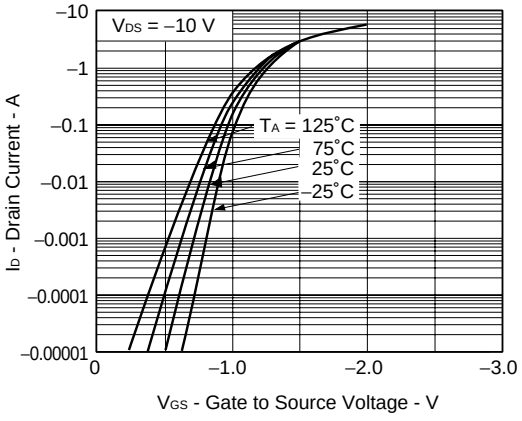
FORWARD BIAS SAFE OPERATING AREA



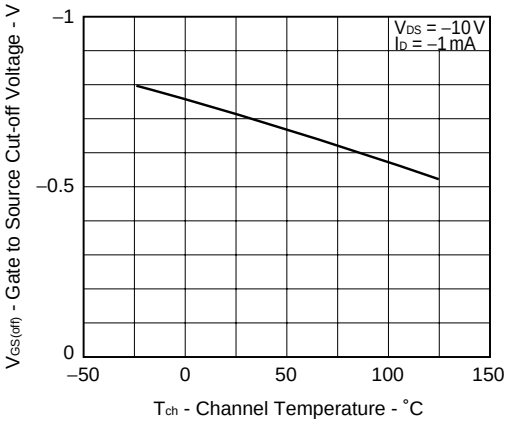
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



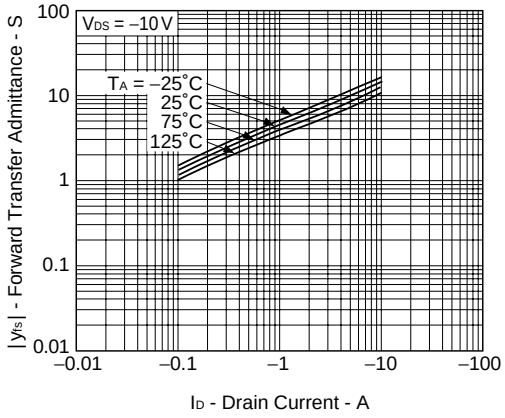
FORWARD TRANSFER CHARACTERISTICS



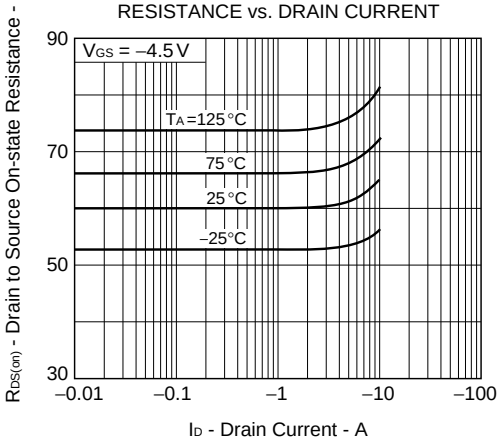
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



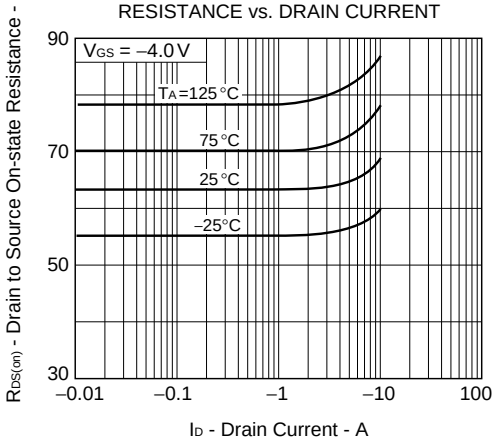
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



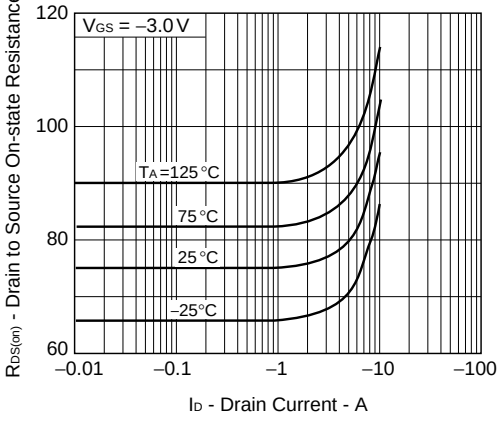
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



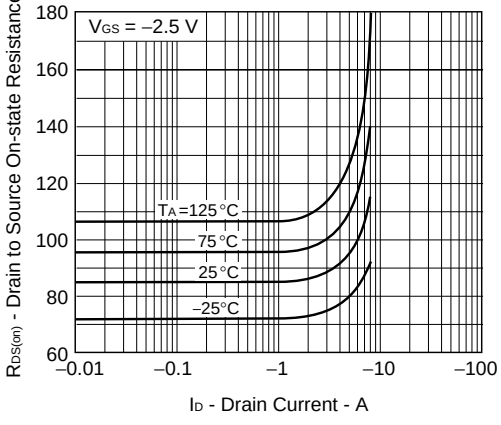
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



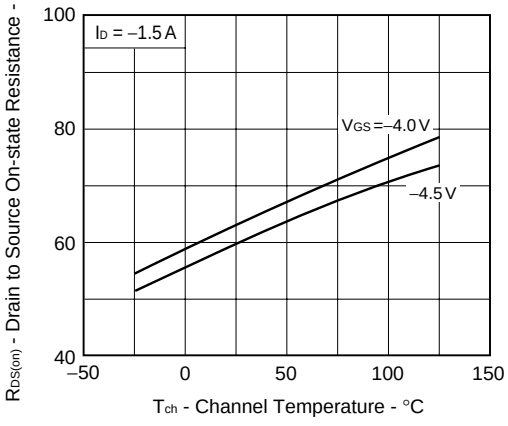
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



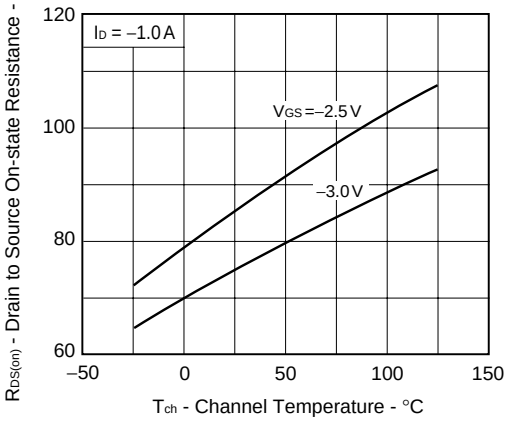
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



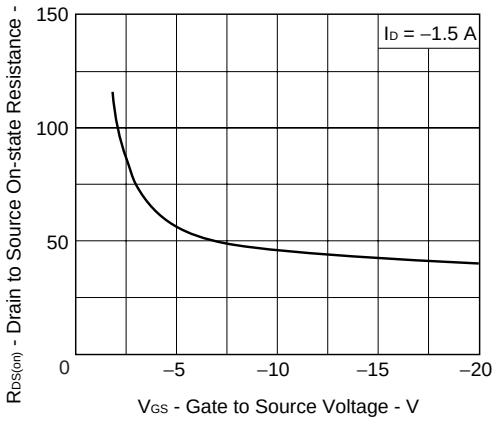
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



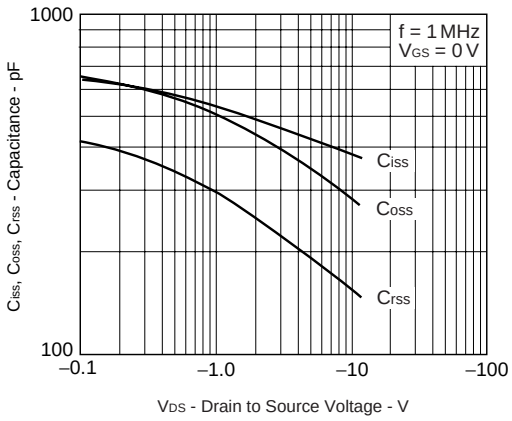
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



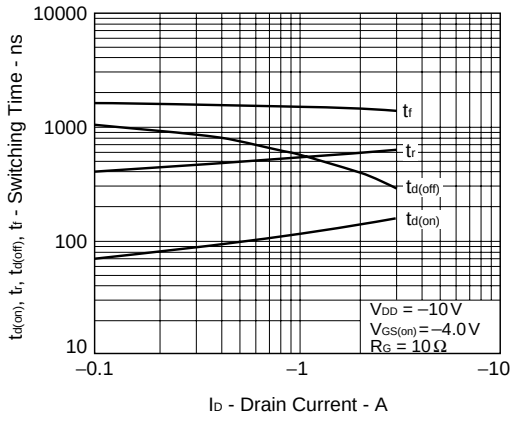
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



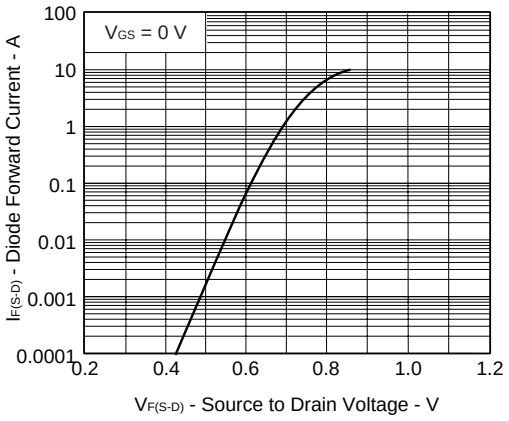
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



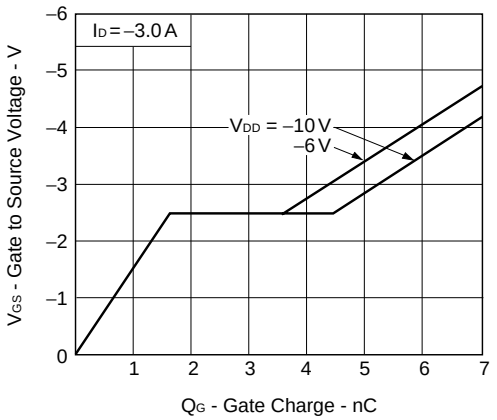
SWITCHING CHARACTERISTICS



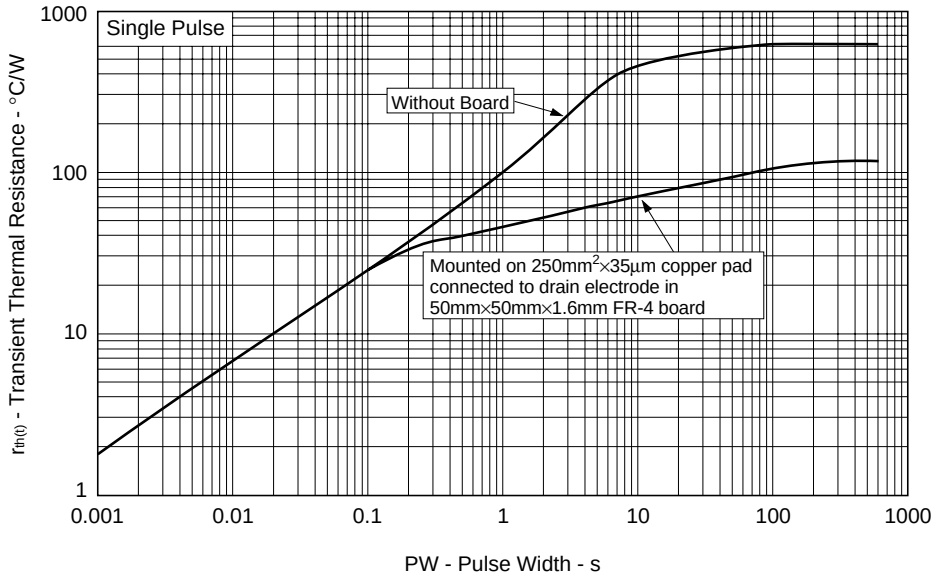
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



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